## 5 V ECL Differential Clock D Flip-Flop

## MC10EL51, MC100EL51

#### Description

The MC10EL/100EL51 is a differential clock D flip-flop with reset. The device is functionally similar to the E151 device with higher performance capabilities. With propagation delays and output transition times significantly faster than the E151 the EL51 is ideally suited for those applications which require the ultimate in AC performance.

The reset input is an asynchronous, level triggered signal. Data enters the master portion of the flip-flop when the clock is LOW and is transferred to the slave, and thus the outputs, upon a positive transition of the clock. The differential clock inputs of the EL51 allow the device to be used as a negative edge triggered flip-flop.

The differential input employs clamp circuitry to maintain stability under open input (pulled down to  $V_{EE}$ ) conditions.

The 100 Series contains temperature compensation.

#### Features

- 475 ps Propagation Delay
- 2.8 GHz Toggle Frequency
- ESD Protection:
  - ◆ >1 kV Human Body Model
  - ♦ > 100 V Machine Model
- PECL Mode Operating Range:
  - $V_{CC} = 4.2 \text{ V}$  to 5.7 V with  $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:
  - $V_{CC} = 0$  V with  $V_{EE} = -4.2$  V to -5.7 V
- Internal Input Pulldown Resistors on D, R, and CLK
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity:
  - Level 1 for SOIC-8 NB
  - For Additional Information, see Application Note <u>AND8003/D</u>
- Flammability Rating:
  - UL 94 V-0 @ 0.125 in, Oxygen Index: 28 to 34
- Transistor Count = 73 devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

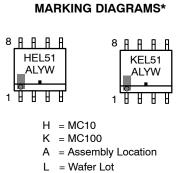


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SOIC-8 NB D SUFFIX CASE 751-07





- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*For additional marking information, refer to Application Note <u>AND8002/D</u>.

#### **ORDERING INFORMATION**

Device	Package	Shipping
MC10EL51DG	SOIC-8 (Pb-Free)	98 Units/Tube
MC100EL51DG	SOIC-8 (Pb-Free)	98 Units/Tube

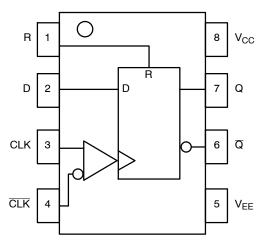


Figure 1. Logic Diagram and Pinout Assignment

#### Table 1. TRUTH TABLE

D*	R*	CLK*	Q**
L	L	Z	LHL
H	L	Z	
X	H	X	

Z = LOW to HIGH Transition

\* Pin will default low when left open.

\*\*Pin will default low when inputs are left open.

#### Table 2. PIN DESCRIPTION

PIN	FUNCTION
R	ECL Reset Input
D	ECL Data Input
CLK, CLK	ECL Clock Inputs
Q, <u>Q</u>	ECL Data Outputs
V <sub>CC</sub>	Positive Supply
$V_{\text{EE}}$	Negative Supply

#### **Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	PECL Mode Power Supply	V <sub>EE</sub> = 0 V		8	V
$V_{EE}$	NECL Mode Power Supply	$V_{CC} = 0 V$		-8	V
VI PECL Mode Input Voltage NECL Mode Input Voltage		V <sub>EE</sub> = 0 V V <sub>CC</sub> = 0 V	$\begin{array}{l} V_I \leq V_{CC} \\ V_I \geq V_{EE} \end{array}$	6 -6	V
I <sub>out</sub> Output Current		Continuous Surge		50 100	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θJC	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

#### Table 4. 10EL SERIES PECL DC CHARACTERISTICS (V<sub>CC</sub> = 5.0 V; V<sub>EE</sub> = 0 V (Note 1))

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		24	29		24	29		24	29	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV
V <sub>IH</sub>	Input HIGH Voltage (Single-Ended)	3770		4110	3870		4190	3940		4280	mV
VIL	Input LOW Voltage (Single-Ended)	3050		3500	3050		3520	3050		3555	mV
V <sub>IHCMR</sub>	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.5		4.6	2.5		4.6	2.5		4.6	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μΑ
Ι <sub>ΙL</sub>	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.25 V / -0.5 V. 2. Outputs are terminated through a 50  $\Omega$  resistor to V<sub>CC</sub> - 2.0 V.

V<sub>IHCMR</sub> min varies 1:1 with V<sub>EE</sub>, V<sub>IHCMR</sub> max varies 1:1 with V<sub>CC</sub>. The V<sub>IHCMR</sub> range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V<sub>PP</sub>min and 1 V.

Table 5. 1	0EL SERIES NECL DC CHARACTE	<b>RISTICS</b> ( $V_{CC} = 0 V; V_{E}$	<sub>E</sub> = -5.0 V (Note 1))	
				1

		–40°C 25°C		85°C							
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	I <sub>EE</sub> Power Supply Current		24	29		24	29		24	29	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	-1080	-990	-890	-980	-895	-810	-910	-815	-720	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	-1950	-1800	-1650	-1950	-1790	-1630	-1950	-1773	-1595	mV
V <sub>IH</sub>	Input HIGH Voltage (Single-Ended)	-1230		-890	-1130		-810	-1060		-720	mV
V <sub>IL</sub>	Input LOW Voltage (Single-Ended)	-1950		-1500	-1950		-1480	-1950		-1445	mV
V <sub>IHCMR</sub> Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)		-2.5		-0.4	-2.5		-0.4	-2.5		-0.4	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μA
Ι <sub>ΙL</sub>	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.25 V / -0.5 V.
Outputs are terminated through a 50 Ω resistor to V<sub>CC</sub> - 2.0 V.
V<sub>IHCMR</sub> min varies 1:1 with V<sub>EE</sub>, V<sub>IHCMR</sub> max varies 1:1 with V<sub>CC</sub>. The V<sub>IHCMR</sub> range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V<sub>PP</sub>min and 1 V.

#### Table 6. 100EL SERIES PECL DC CHARACTERISTICS (V<sub>CC</sub> = 5.0 V; V<sub>EE</sub> = 0 V (Note 1))

		–40°C 25°C						85°C			Ι
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		24	29		24	29		30	36	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV
V <sub>IH</sub>	Input HIGH Voltage (Single-Ended)	3835		4120	3835		4120	3835		4120	mV
VIL	Input LOW Voltage (Single-Ended)	3190		3525	3190		3525	3190		3525	mV
V <sub>IHCMR</sub>	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	2.5		4.6	2.5		4.6	2.5		4.6	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μA
IIL	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V\_{CC}^{-} V\_EE can vary +0.8 V / –0.5 V.

Outputs are terminated through a 50 Ω resistor to V<sub>CC</sub> – 2.0 V.
V<sub>IHCMR</sub> min varies 1:1 with V<sub>EE</sub>, V<sub>IHCMR</sub> max varies 1:1 with V<sub>CC</sub>. The V<sub>IHCMR</sub> range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V<sub>PP</sub>min and 1 V.

			<b>−40°C</b>			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
$I_{EE}$	Power Supply Current		24	29		24	29		30	36	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV
V <sub>IH</sub>	Input HIGH Voltage (Single-Ended)	-1165		-880	-1165		-880	-1165		-880	mV
V <sub>IL</sub>	Input LOW Voltage (Single-Ended)	-1810		-1475	-1810		-1475	-1810		-1475	mV
VIHCMR	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 3)	-2.5		-0.4	-2.5		-0.4	-2.5		-0.4	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μA
۱ <sub>IL</sub>	Input LOW Current	0.5			0.5			0.5			μA

Table 7. 100EL SERIES NECL DC CHARACTERISTICS (V<sub>CC</sub> = 0 V; V<sub>FF</sub> = -5.0 V (Note 1))

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.8 V / -0.5 V. 2. Outputs are terminated through a 50  $\Omega$  resistor to V<sub>CC</sub> - 2.0 V.

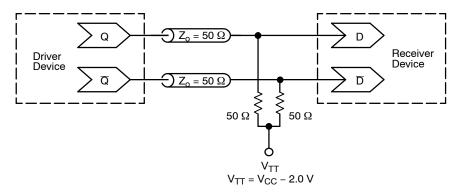
3. VIHCMR min varies 1:1 with VEE, VIHCMR max varies 1:1 with VCC. The VIHCMR range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V<sub>PP</sub>min and 1 V.

			-40°C			25°C		85°C			
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
fmax	Maximum Toggle Frequency	1.8	2.8		2.2	2.8		2.2	2.8		GHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay to Output CLK R	325 305	465 455	605 605	385 355	475 465	565 565	440 410	530 510	620 620	ps
t <sub>S</sub>	Setup Time	150	0		150	0		150	0		ps
t <sub>H</sub>	Hold Time	250	100		250	100		250	100		ps
t <sub>RR</sub>	Reset Recovery	400	200		400	200		400	200		ps
t <sub>PW</sub>	Minimum Pulse Width CLK, Reset	400			400			400			ps
V <sub>PP</sub>	Input Swing (Note 2)	150		1000	150		1000	150		1000	mV
t <sub>JITTER</sub>	Cycle-to-Cycle Jitter		TBD			TBD			TBD		ps
t <sub>r</sub> t <sub>f</sub>	Output Rise/Fall Times Q (20% - 80%)	100	225	350	100	225	350	100	225	350	ps

Table 8. AC CHARACTERISTICS (V<sub>CC</sub>= 5.0 V; V<sub>EE</sub>= 0.0 V or V<sub>CC</sub>= 0.0 V; V<sub>EE</sub>= -5.0 V (Note 1))

10 Series: V<sub>EE</sub> can vary +0.25 V / -0.5 V. 100 Series: V<sub>EE</sub> can vary +0.8 V / -0.5 V.

2. V<sub>PP/</sub>min) is minimum input swing for which AC parameters guaranteed. The device has a DC gain of ~40.





#### **Resource Reference of Application Notes**

- AN1405/D - ECL Clock Distribution Techniques
- AN1406/D - Designing with PECL (ECL at +5.0 V)
- AN1503/D - ECLinPS<sup>™</sup> I/O SPiCE Modeling Kit
- AN1504/D - Metastability and the ECLinPS Family
- AN1568/D - Interfacing Between LVDS and ECL
- AN1672/D - The ECL Translator Guide
- AND8001/D Odd Number Counters Design
- Marking and Date Codes AND8002/D
- AND8020/D - Termination of ECL Logic Devices
- Interfacing with ECLinPS AND8066/D
- AND8090/D AC Characteristics of ECL Devices

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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

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8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

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STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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COLLECTOR, #1

COLLECTOR, #1

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